

2SB0939 (2SB939), 2SB0939A (2SB939A)

Silicon PNP epitaxial planar type Darlington

For midium-speed power switching

Complementary to 2SD1262, 2SD1262A

■ Features

- High forward current transfer ratio h_{FE}
- High-speed switching
- N type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.

■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

Parameter		Symbol	Rating	Unit
Collector-base voltage (Emitter open)	2SB0939	V_{CBO}	−60	V
	2SB0939A		−80	
Collector-emitter voltage (Base open)	2SB0939	V_{CEO}	−60	V
	2SB0939A		−80	
Emitter-base voltage (Collector open)		V_{EBO}	−7	V
Collector current		I_C	−8	A
Peak collector current		I_{CP}	−12	A
Collector power dissipation	$T_a = 25^{\circ}\text{C}$	P_C	45	W
			1.3	
Junction temperature		T_j	150	$^{\circ}\text{C}$
Storage temperature		T_{stg}	−55 to +150	$^{\circ}\text{C}$

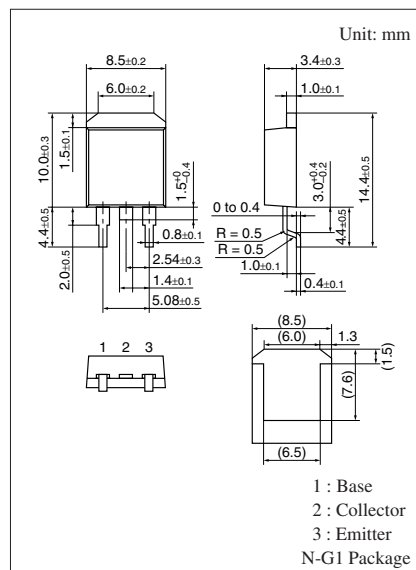
■ Electrical Characteristics $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	2SB0939 2SB0939A	V_{CEO} $I_C = -30\text{ mA}, I_B = 0$	-60			V
			-80			
Collector-base cut-off current (Emitter open)	2SB0939 2SB0939A	I_{CBO} $V_{CB} = -60\text{ V}, I_E = 0$ $V_{CB} = -80\text{ V}, I_E = 0$			-100	μA
					-100	
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = -7\text{ V}, I_C = 0$			-2	mA
Forward current transfer ratio	h_{FE1}^* h_{FE2}	$V_{CE} = -3\text{ V}, I_C = -4\text{ A}$ $V_{CE} = -3\text{ V}, I_C = -8\text{ A}$	2000		10 000	—
			500			
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -4\text{ A}, I_B = -8\text{ mA}$			-2	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -4\text{ A}, I_B = -8\text{ mA}$			-1.5	V
Transition frequency	f_T	$V_{CE} = -10\text{ V}, I_C = -0.5\text{ A}, f = 1\text{ MHz}$		20		MHz
Turn-on time	t_{on}	$I_C = -4\text{ A},$		0.5		μs
Strage time	t_{stg}	$I_{B1} = -8\text{ mA}, I_{B2} = 8\text{ mA}$		2		μs
Fall time	t_f	$V_{CC} = -50\text{ V}$		1		μs

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

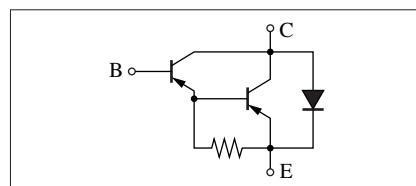
2. *: Rank classification

Rank	Q	P
h_{FE1}	2000 to 5000	4000 to 10000

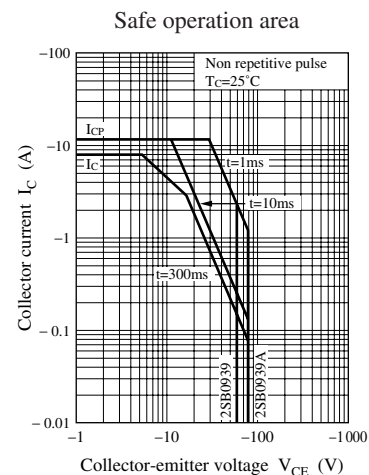
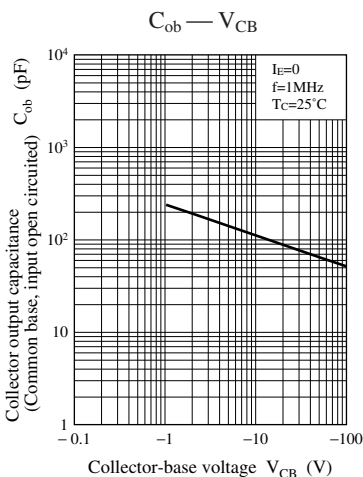
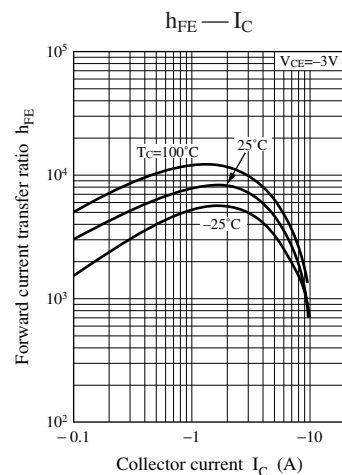
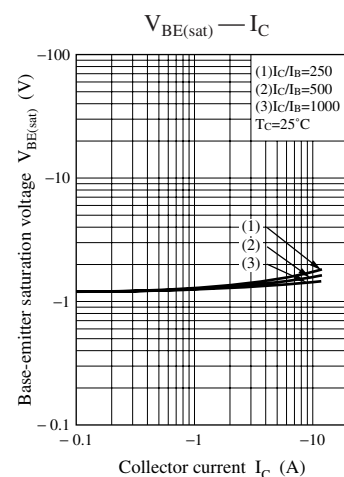
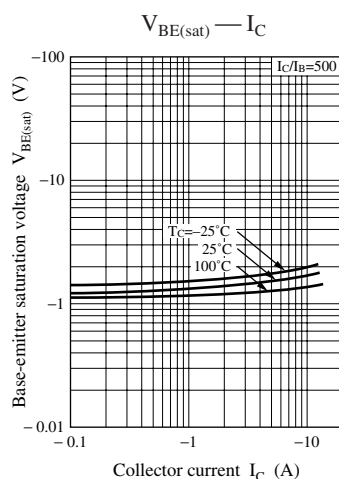
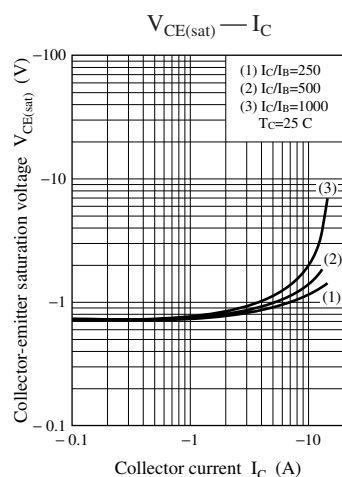
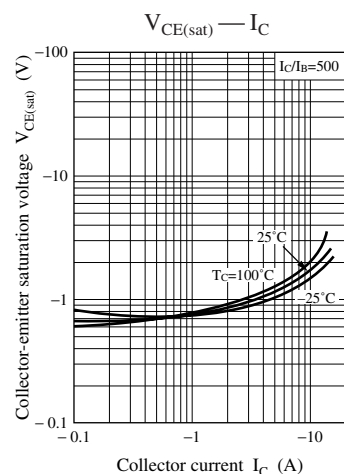
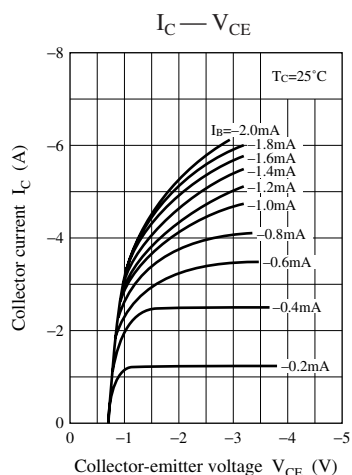
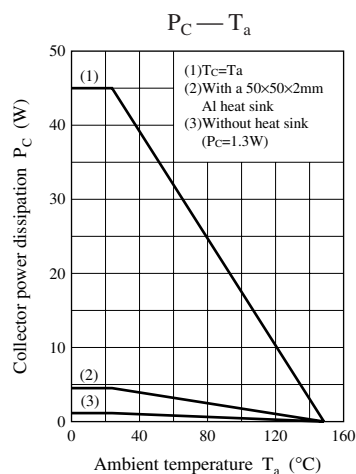


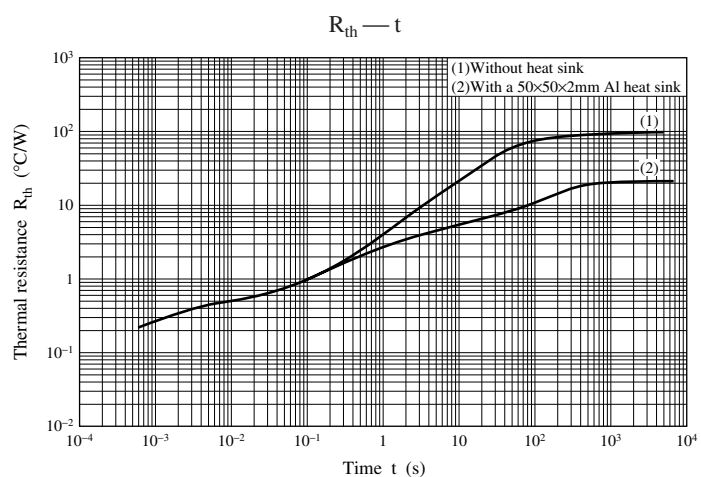
Note) Self-supported type package is also prepared.

Internal Connection



Note) The part number in the parenthesis shows conventional part number.





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